

FIG. 1

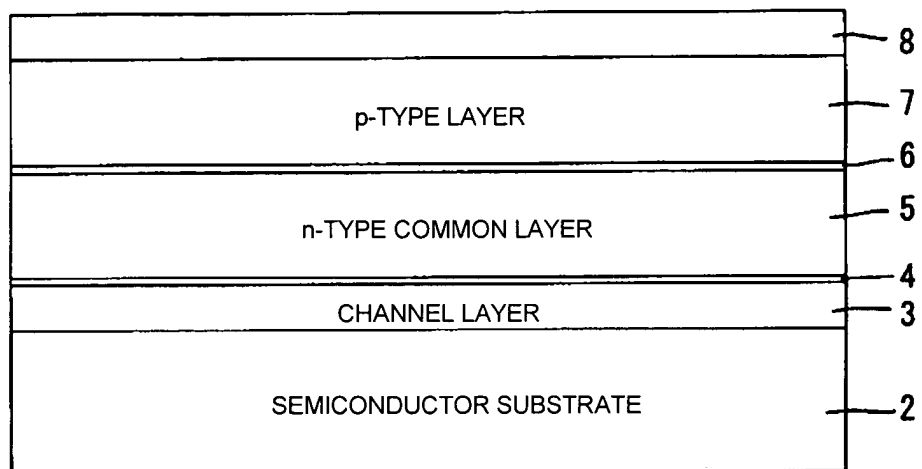


FIG. 2

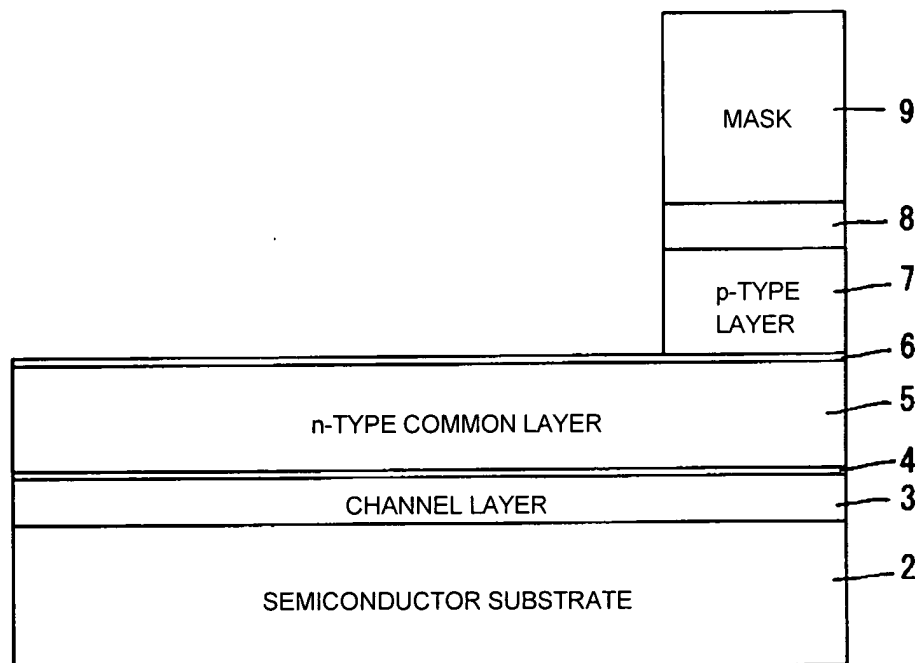


FIG. 3

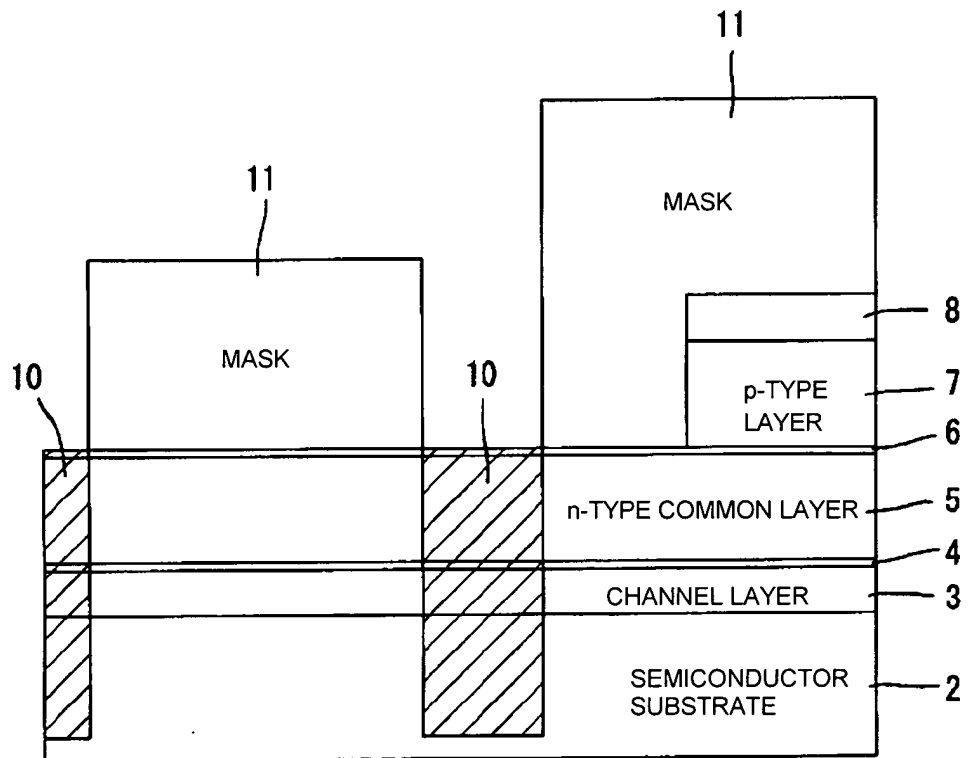


FIG. 4

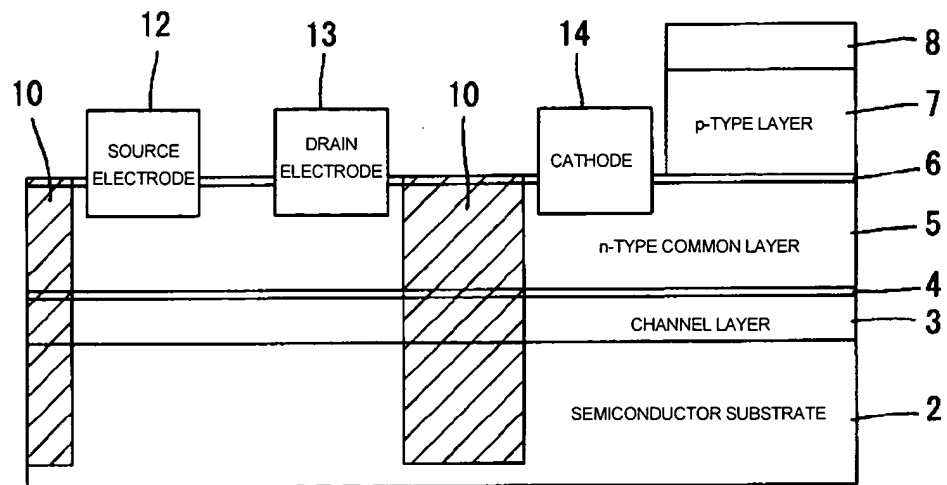
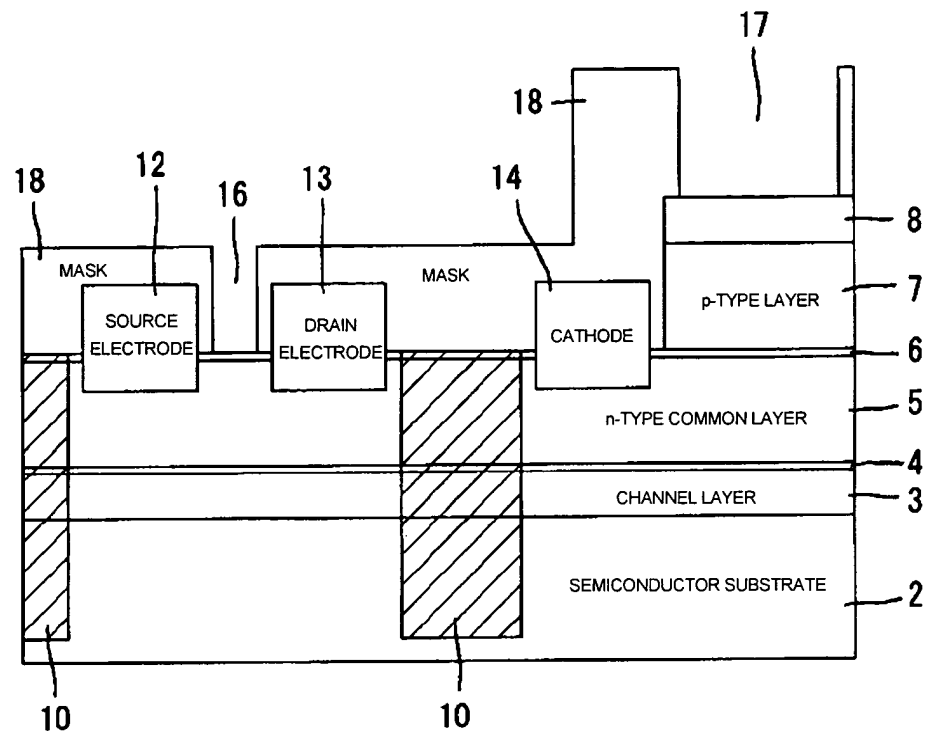


FIG. 5



This cross-sectional view shows a semiconductor device with a p-type layer (7) and an n-type common layer (5). The device includes a source electrode (12) and a drain electrode (13), both covered by a mask (18). A cathode (14) is also present. The device is built on a semiconductor substrate (2) with a channel layer (3) and an n-type common layer (5). The p-type layer (7) is on top of the n-type common layer (5). The source electrode (12) and drain electrode (13) are separated by a channel layer (3). The cathode (14) is on the right side. The device is covered by a mask (18). The p-type layer (7) is on top of the n-type common layer (5). The source electrode (12) and drain electrode (13) are separated by a channel layer (3). The cathode (14) is on the right side. The device is covered by a mask (18). The p-type layer (7) is on top of the n-type common layer (5). The source electrode (12) and drain electrode (13) are separated by a channel layer (3). The cathode (14) is on the right side. The device is covered by a mask (18).



FIG. 8

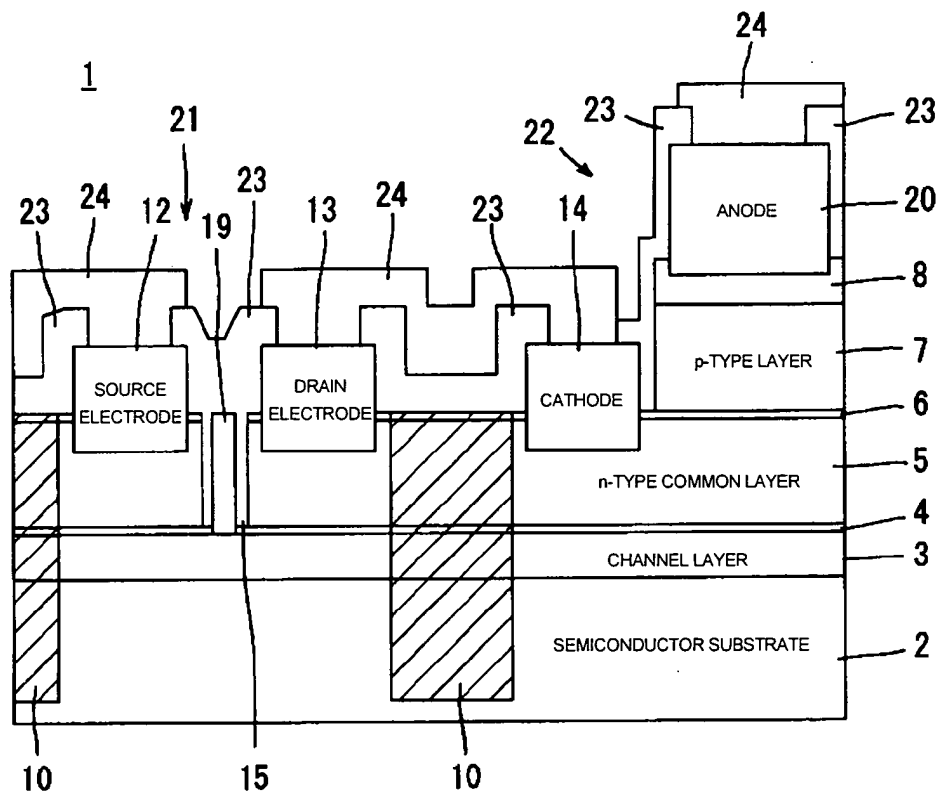




FIG. 9

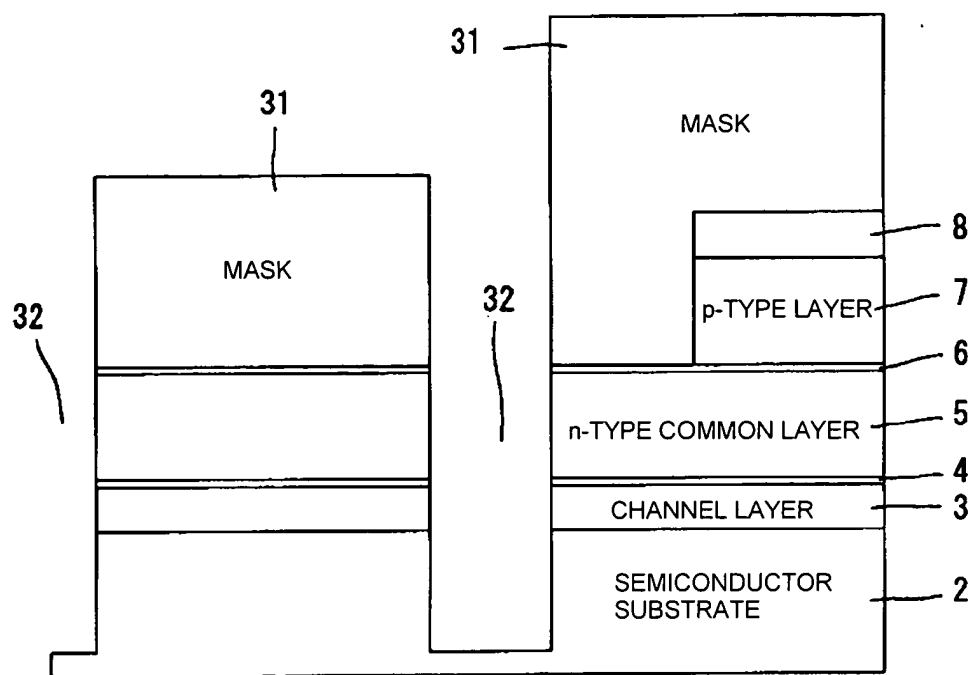


FIG. 10

